

P-Channel Power MOSFET

-40V, -22A, 15mΩ

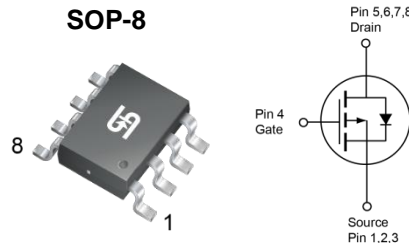
FEATURES

- Low $R_{DS(on)}$ to minimize conductive losses
- Logic level
- Low gate charge for fast power switching
- 100% UIS and R_g tested
- Compliant to RoHS directive 2011/65/EU and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21

KEY PERFORMANCE PARAMETERS			
PARAMETER		VALUE	UNIT
V_{DS}		-40	V
$R_{DS(on)}$ (max)	$V_{GS} = -10V$	15	mΩ
	$V_{GS} = -4.5V$	21	
Q_g		23	nC

APPLICATIONS

- POL
- Load Switch
- Motor Drives



Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	-40	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ^(Note 1)	$T_C = 25^\circ\text{C}$	I_D	-22	A
	$T_A = 25^\circ\text{C}$		-9	
Pulsed Drain Current		I_{DM}	-88	A
Single Pulse Avalanche Current ^(Note 2)		I_{AS}	-27	A
Single Pulse Avalanche Energy ^(Note 2)		E_{AS}	109	mJ
Total Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	12.5	W
	$T_C = 125^\circ\text{C}$		2.5	
Total Power Dissipation	$T_A = 25^\circ\text{C}$	P_D	2.2	W
	$T_A = 125^\circ\text{C}$		0.4	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	- 55 to +150	$^\circ\text{C}$

THERMAL PERFORMANCE			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction to Case Thermal Resistance	$R_{\theta JC}$	10	$^\circ\text{C/W}$
Junction to Ambient Thermal Resistance	$R_{\theta JA}$	57	$^\circ\text{C/W}$

Thermal Performance Note: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\theta JA}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.

ELECTRICAL SPECIFICATIONS ($T_A = 25^\circ\text{C}$ unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-40	--	--	V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250\mu A$	$V_{GS(TH)}$	-1	-1.65	-2.5	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = -40V$	I_{DSS}	--	--	-1	μA
	$V_{GS} = 0V, V_{DS} = -32V$ $T_J = 125^\circ\text{C}$		--	--	-100	
Drain-Source On-State Resistance (Note 3)	$V_{GS} = -10V, I_D = -9A$	$R_{DS(on)}$	--	11	15	m Ω
	$V_{GS} = -4.5V, I_D = -8A$		--	15	21	
Forward Transconductance (Note 3)	$V_{DS} = -5V, I_D = -9A$	g_{fs}	--	29	--	S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = -10V,$ $V_{DS} = -20V, I_D = 9A$	Q_g	--	48	--	nC
Total Gate Charge	$V_{GS} = -4.5V,$ $V_{DS} = -20V, I_D = -9A$	Q_g	--	23	--	
Gate-Source Charge		Q_{gs}	--	9	--	
Gate-Drain Charge		Q_{gd}	--	8.5	--	
Input Capacitance	$V_{GS} = 0V, V_{DS} = -20V$ $f = 1.0\text{MHz}$	C_{iss}	--	2783	--	pF
Output Capacitance		C_{oss}	--	269	--	
Reverse Transfer Capacitance		C_{rss}	--	142	--	
Gate Resistance	$f = 1.0\text{MHz}$	R_g	2	6	12	Ω
Switching (Note 4)						
Turn-On Delay Time	$V_{GS} = -10V, V_{DS} = -20V,$ $I_D = -9A, R_G = 2\Omega,$	$t_{d(on)}$	--	7	--	ns
Turn-On Rise Time		t_r	--	45	--	
Turn-Off Delay Time		$t_{d(off)}$	--	67	--	
Turn-Off Fall Time		t_f	--	59	--	
Source-Drain Diode						
Forward Voltage (Note 3)	$V_{GS} = 0V, I_S = -9A$	V_{SD}	--	--	-1	V
Reverse Recovery Time	$I_S = -9A,$ $di/dt = 100A/\mu s$	t_{rr}	--	19	--	ns
Reverse Recovery Charge		Q_{rr}	--	11	--	nC

Notes:

- Silicon limited current only.
- $L = 0.3\text{mH}, V_{GS} = -10V, V_{DD} = -25V, R_G = 25\Omega, I_{AS} = -27A,$ Starting $T_J = 25^\circ\text{C}$
- Pulse test: Pulse Width $\leq 300\mu s,$ duty cycle $\leq 2\%$.
- Switching time is essentially independent of operating temperature.

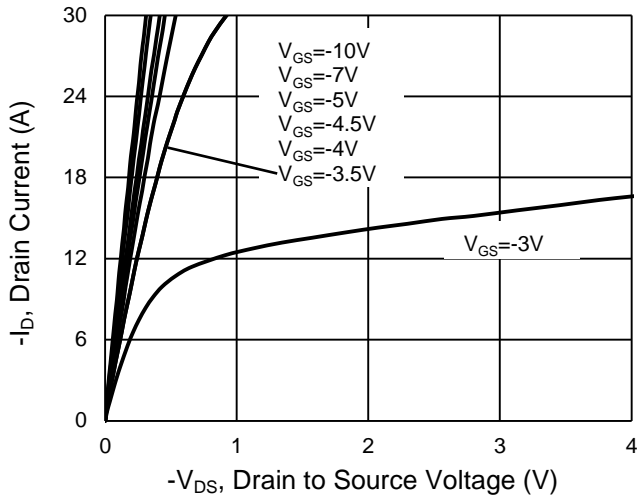
ORDERING INFORMATION

PART NO.	PACKAGE	PACKING
TSM150P04LCS RLG	SOP-8	2,500pcs / 13" Reel

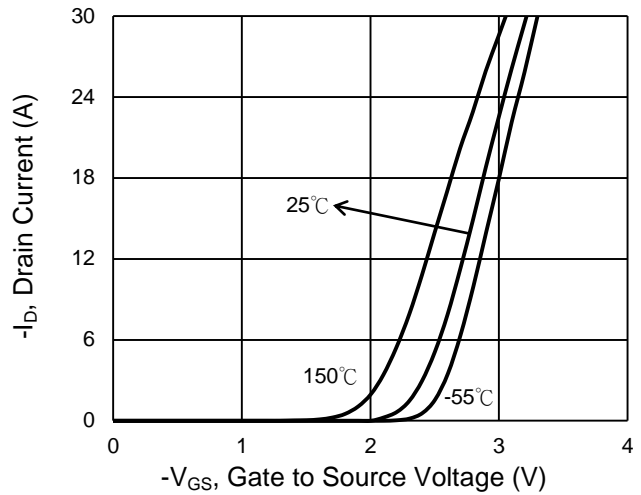
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

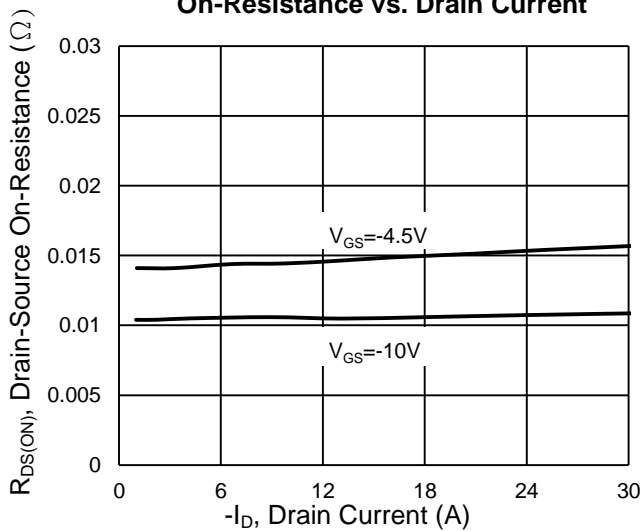
Output Characteristics



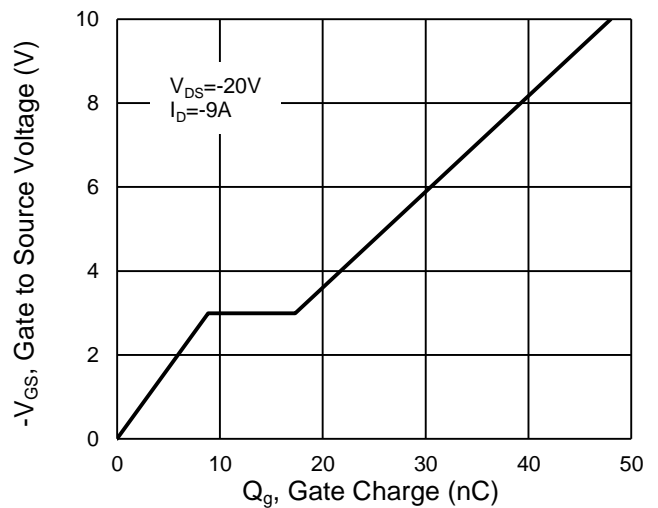
Transfer Characteristics



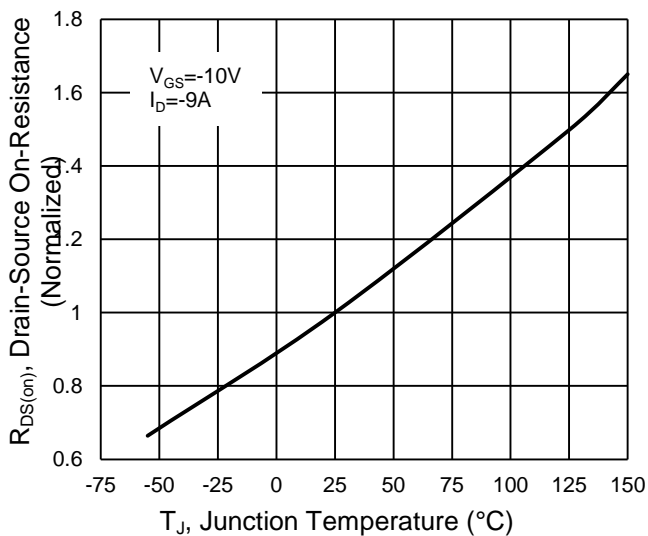
On-Resistance vs. Drain Current



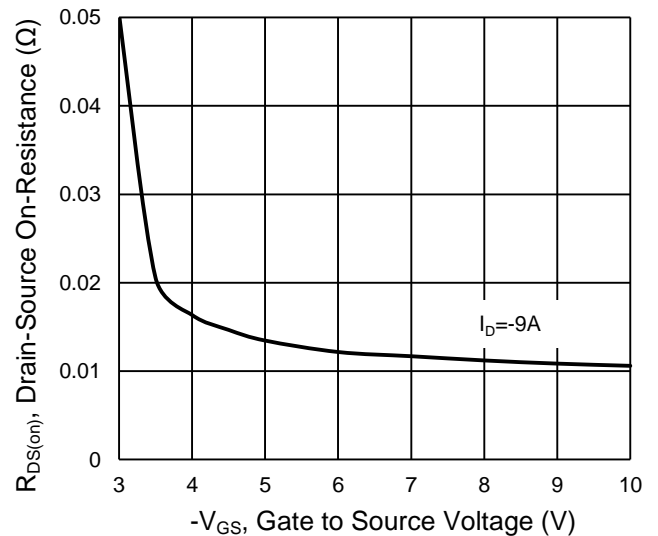
Gate-Source Voltage vs. Gate Charge



On-Resistance vs. Junction Temperature



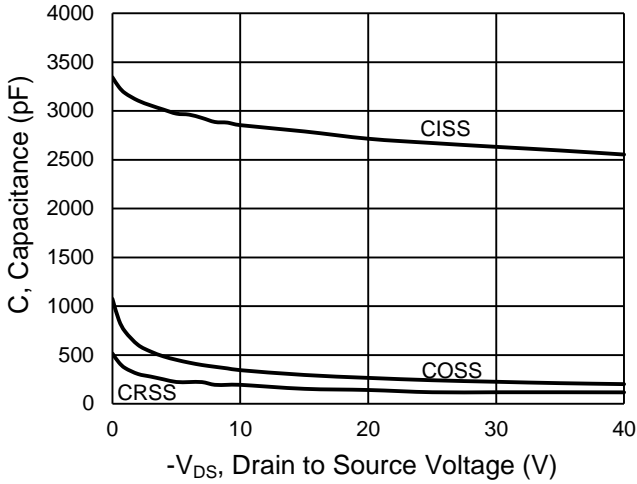
On-Resistance vs. Gate-Source Voltage



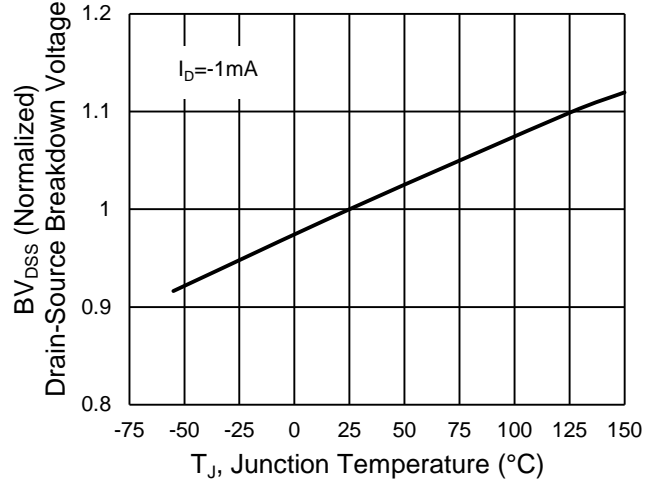
CHARACTERISTICS CURVES

($T_A = 25^\circ\text{C}$ unless otherwise noted)

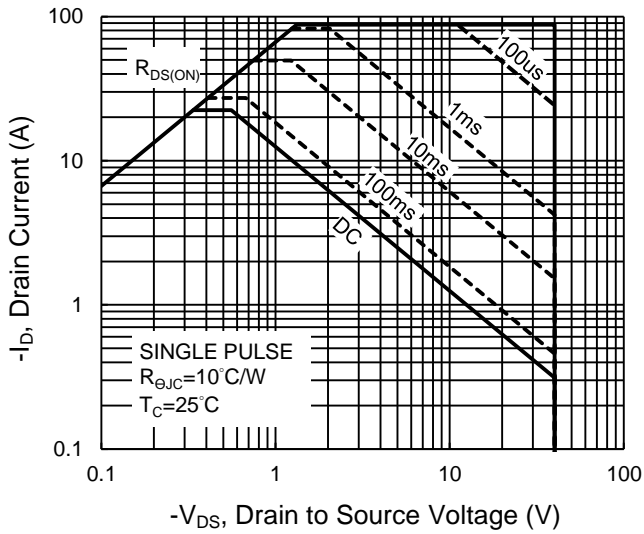
Capacitance vs. Drain-Source Voltage



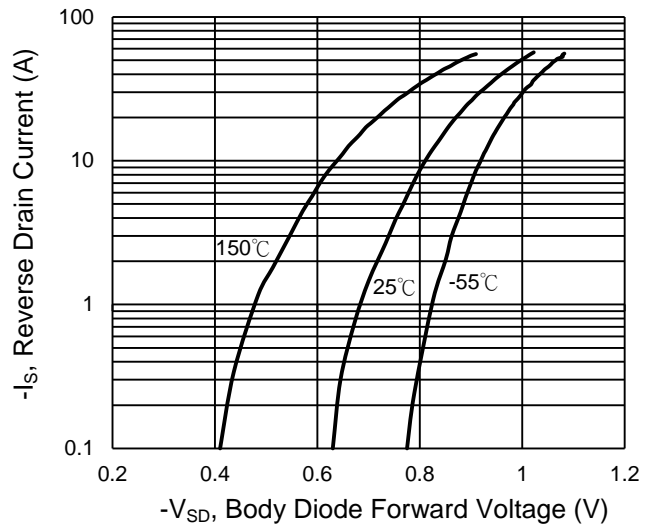
BV_{DSS} vs. Junction Temperature



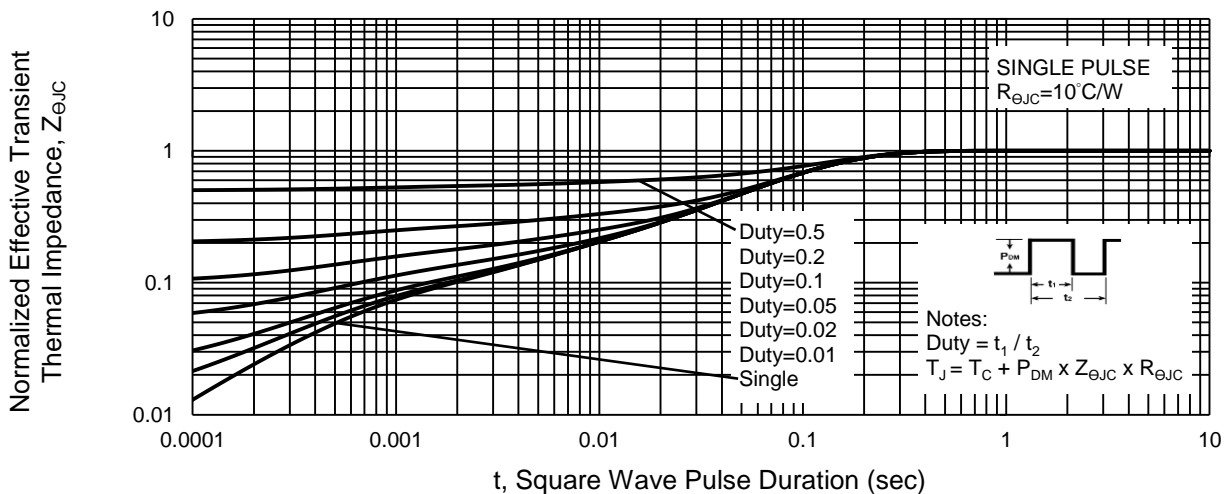
Maximum Safe Operating Area, Junction-to-Case



Source-Drain Diode Forward Current vs. Voltage

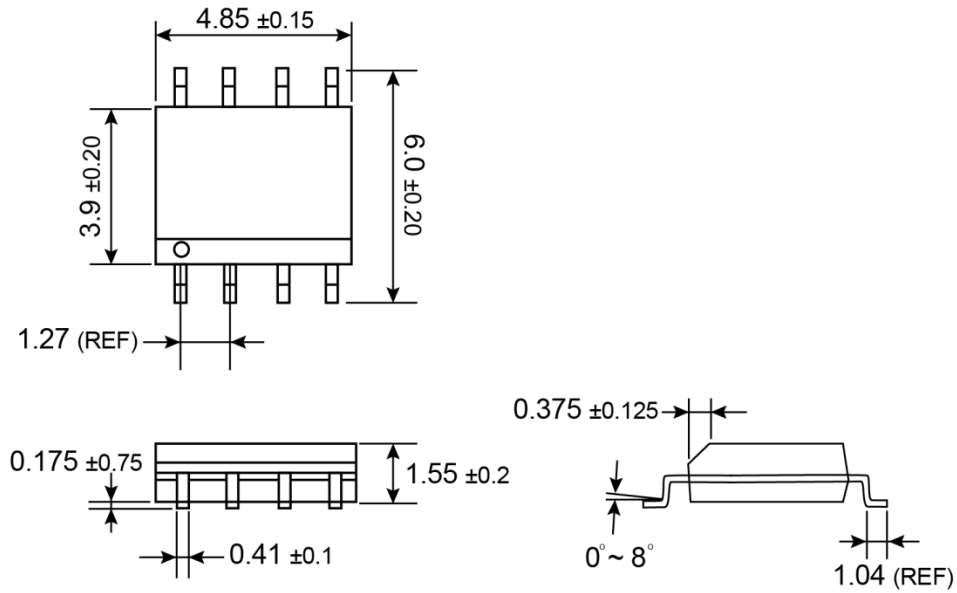


Normalized Thermal Transient Impedance, Junction-to-Case

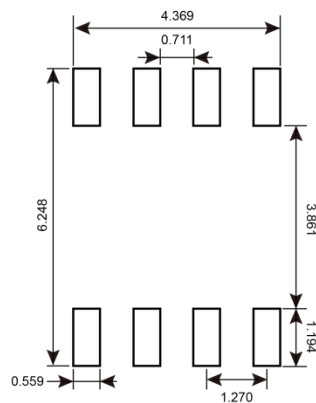


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

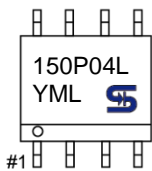
SOP-8



SUGGESTED PAD LAYOUT (Unit: Millimeters)



MARKING DIAGRAM



- Y** = Year Code
- M** = Month Code
- O** =Jan **P** =Feb **Q** =Mar **R** =Apr
- S** =May **T** =Jun **U** =Jul **V** =Aug
- W** =Sep **X** =Oct **Y** =Nov **Z** =Dec
- L** = Lot Code (1~9, A~Z)

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